

## Automotive MOSFET

## OptiMOS™ 6 Power-Transistor



## Features

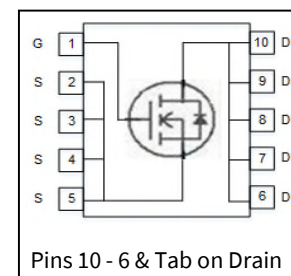
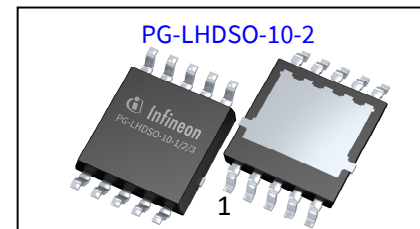
- OptiMOS™ power MOSFET for automotive applications
- N-channel – Enhancement mode – Normal Level
- Extended qualification beyond AEC-Q101
- Enhanced electrical testing
- Robust design
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- RoHS compliant
- 100% Avalanche tested
- Top Side Cooling

## Potential applications

General automotive applications.

## Product validation

Qualified for automotive applications. Product validation according to AEC-Q101.



## Product Summary

$V_{DS}$	40	V
$R_{DS(on)}$	0.89	mΩ
$I_D$ (chip limited)	330	A

Type	Package	Marking
IAUCN04S6N009T	PG-LHDSO-10-2	6B4

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## Maximum ratings

at  $T_j=25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	$I_D$	$V_{GS}=10\text{ V}$ , Chip limitation <sup>1,2)</sup>	330	A
		$V_{GS}=10\text{V}$ , DC current	120	
		$T_a=85\text{ °C}$ , $V_{GS}=10\text{ V}$ , $R_{thJA}$ on $2s2p$ <sup>2,4)</sup>	70	
Pulsed drain current <sup>2)</sup>	$I_{D,pulse}$	$T_C=25\text{ °C}$ , $t_p=100\text{ }\mu\text{s}$	1000	
Avalanche energy, single pulse <sup>2)</sup>	$E_{AS}$	$I_D=60\text{ A}$	380	mJ
Avalanche current, single pulse	$I_{AS}$	–	95	A
Gate source voltage	$V_{GS}$	–	$\pm 20$	V
Power dissipation	$P_{tot}$	$T_C=25\text{ °C}$	178	W
Operating and storage temperature	$T_j, T_{stg}$	–	-55 ... +175	°C

**Thermal characteristics<sup>2)</sup>**

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal resistance, junction - case	$R_{thJC}$	–	–	0.42	0.84	K/W
Thermal characterization parameter, source pin <sup>5)</sup>	$\psi_{source}$		–	5.3	–	
Thermal characterization parameter, drain pin <sup>6)</sup>	$\psi_{drain}$		–	5.3	–	
Thermal resistance, junction - heatsink <sup>4)</sup>	$R_{thJH}$		–	6.9	–	
Thermal resistance, junction - ambient <sup>3)</sup>	$R_{thJA}$	–	–	49	–	

**Electrical characteristics**

 at  $T_j=25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Static characteristics**

Drain-source breakdown voltage	$V_{(Br)DSS}$	$V_{GS}=0\text{ V}$ , $I_D=1\text{ mA}$	40	–	–	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_D=90\text{ }\mu\text{A}$	2.2	2.6	3.0	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=40\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=25\text{ °C}$	–	–	1	$\mu\text{A}$
		$V_{DS}=40\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=125\text{ °C}^{2)}$	–	–	25	
Gate-source leakage current	$I_{GSS}$	$V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$	–	–	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=7\text{ V}$ , $I_D=60\text{ A}$	–	0.95	1.1	m $\Omega$
		$V_{GS}=10\text{ V}$ , $I_D=60\text{ A}$	–	0.79	0.89	
Gate resistance <sup>2)</sup>	$R_G$	–	–	0.9	–	$\Omega$

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
<b>Dynamic characteristics<sup>2)</sup></b>						
Input capacitance	$C_{iss}$	$V_{GS}=0\text{ V}, V_{DS}=25\text{ V}, f=1\text{ MHz}$	-	5650	7345	pF
Output capacitance	$C_{oss}$		-	1700	2210	
Reverse transfer capacitance	$C_{rss}$		-	80	120	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=20\text{ V}, V_{GS}=10\text{ V},$ $I_D=120\text{ A}, R_G=3.5\ \Omega$	-	10	-	ns
Rise time	$t_r$		-	6	-	
Turn-off delay time	$t_{d(off)}$		-	25	-	
Fall time	$t_f$		-	12	-	

**Gate Charge Characteristics<sup>2)</sup>**

Gate to source charge	$Q_{gs}$	$V_{DD}=32\text{ V}, I_D=120\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	23	30	nC
Gate to drain charge	$Q_{gd}$		-	17	26	
Gate charge total	$Q_g$		-	80	104	
Gate plateau voltage	$V_{plateau}$		-	4.1	-	V

**Reverse Diode**

Diode continuous forward current <sup>2)</sup>	$I_S$	$T_C=25\text{ }^\circ\text{C}$	-	-	120	A
Diode pulse current <sup>2)</sup>	$I_{S,pulse}$	$T_C=25\text{ }^\circ\text{C}, t_p=100\ \mu\text{s}$	-	-	1000	
Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=60\text{ A}, T_j=25\text{ }^\circ\text{C}$	-	0.8	1.1	V
Reverse recovery time <sup>2)</sup>	$t_{rr}$	$V_R=20\text{ V}, I_F=50\text{ A},$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	41	-	ns
Reverse recovery charge <sup>2)</sup>	$Q_{rr}$		-	38	-	nC

<sup>1)</sup> Practically the current is limited by the overall system design including the customer-specific PCB.

<sup>2)</sup> The parameter is not subject to production testing – specified by design.

<sup>3)</sup> Device on 2s2p FR4 PCB defined in accordance with JEDEC standards (JESD51-5, -7). PCB is vertical in still air.

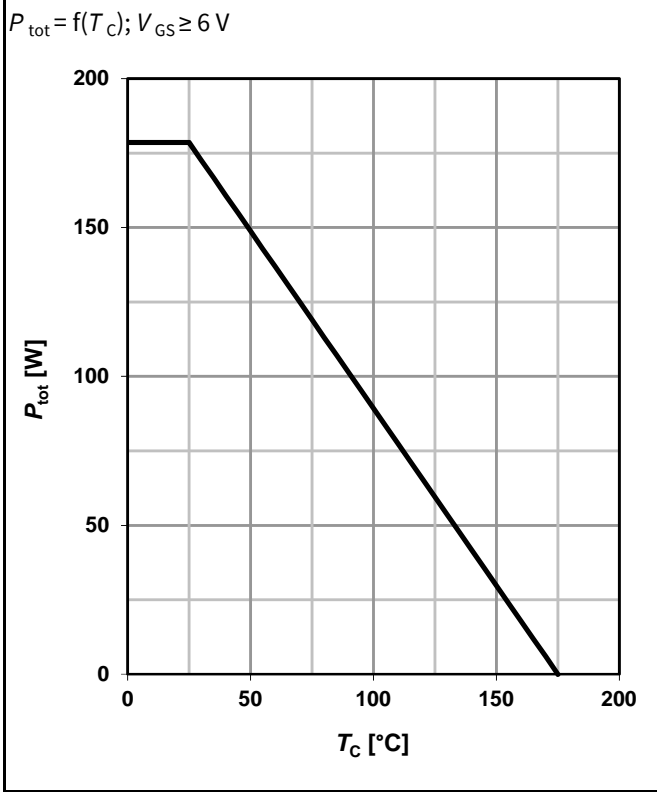
<sup>4)</sup> Device on 2s2p FR4 PCB defined in accordance with JEDEC standards (JESD51-5, -7) without thermal vias, heatsink of 71x110x2 mm is attached through 3 W/(m\*K) 400µm to top side pad. Heatsink fixed to 85°C ambient temperature.

<sup>5)</sup> Thermal characterization parameter, calculated as  $\psi_{source} = (T_{source} - T_{ambient})/P_{dis}$  in condition of 4). Used to determine PCB temperature at source pins for given power.

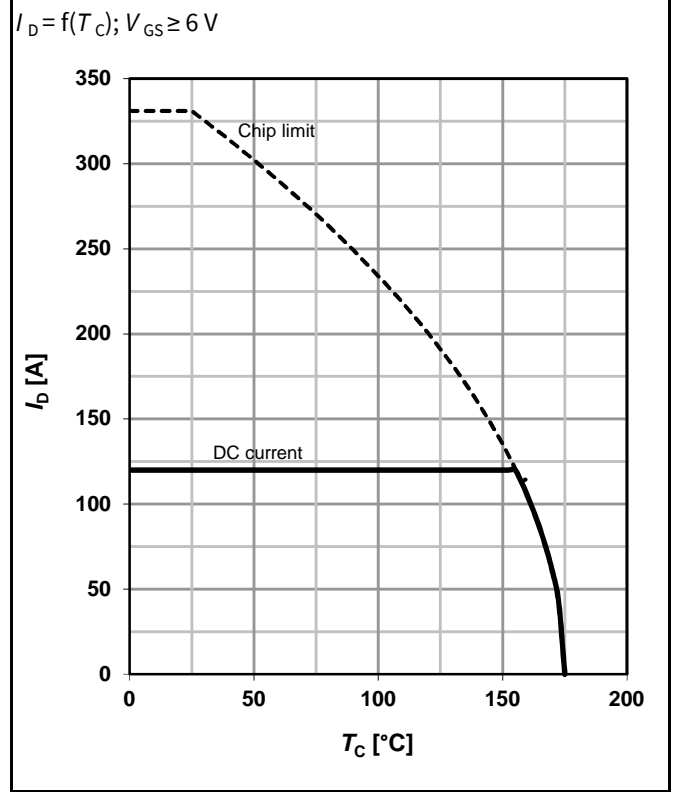
<sup>6)</sup> Thermal characterization parameter, calculated as  $\psi_{drain} = (T_{drain} - T_{ambient})/P_{dis}$  in condition of 4). Used to determine PCB temperature at drain pins for given power.

## Electrical characteristics diagrams

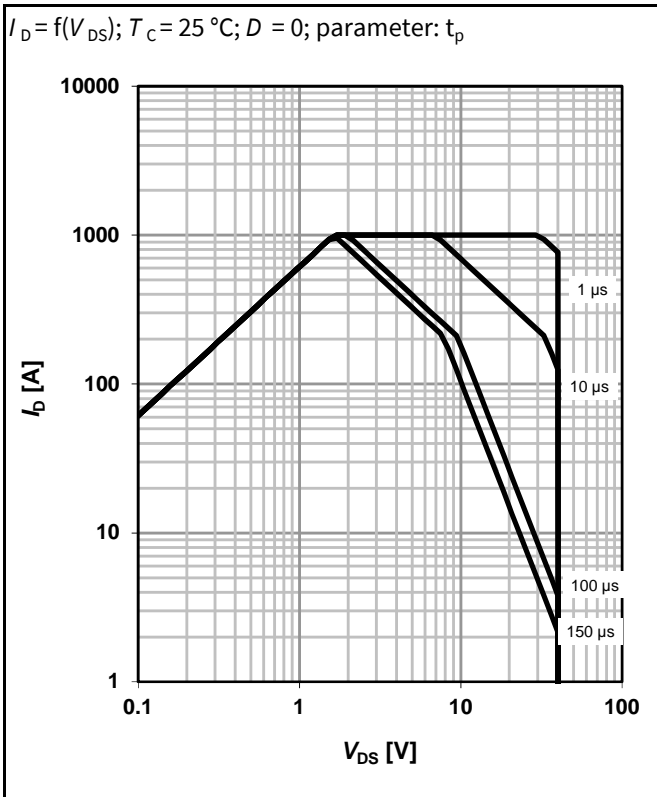
### 1 Power dissipation



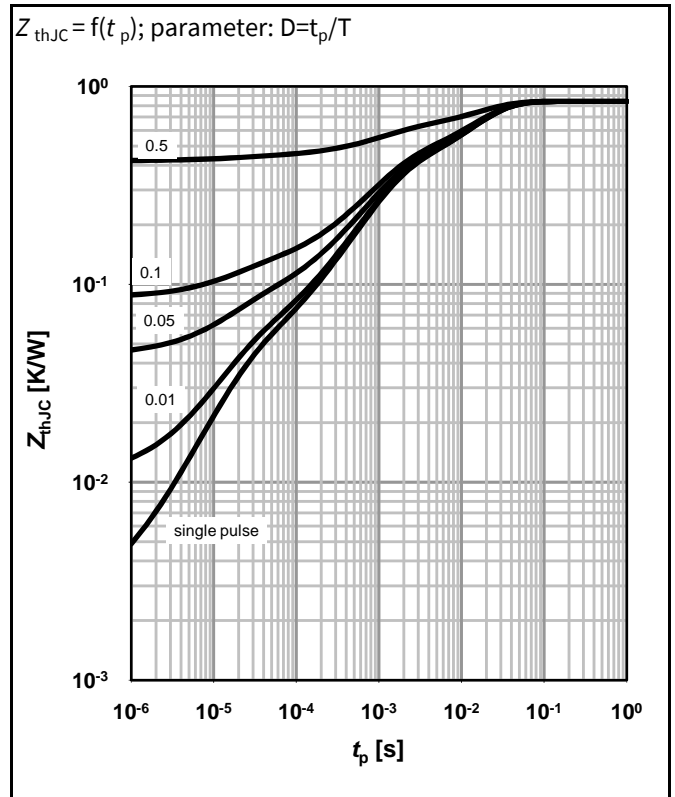
### 2 Drain current



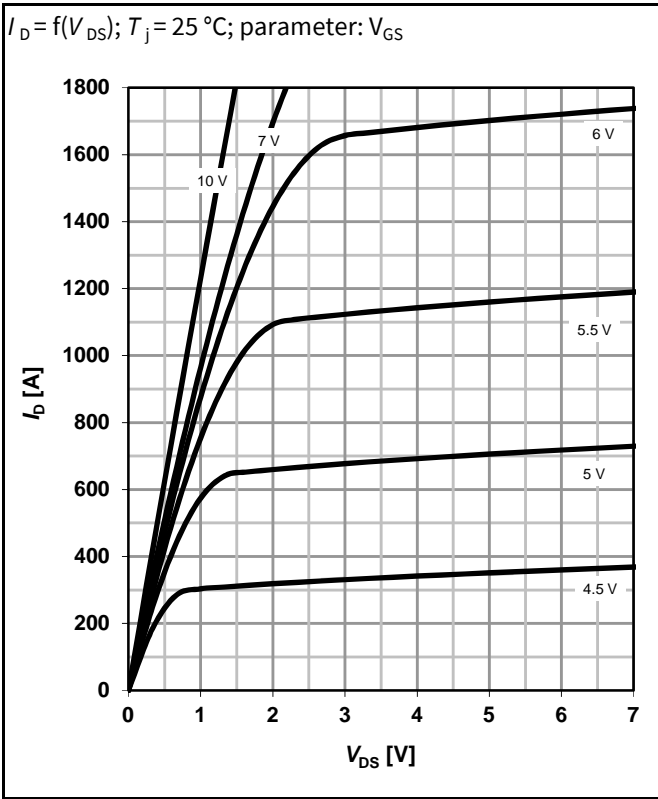
### 3 Safe operating area



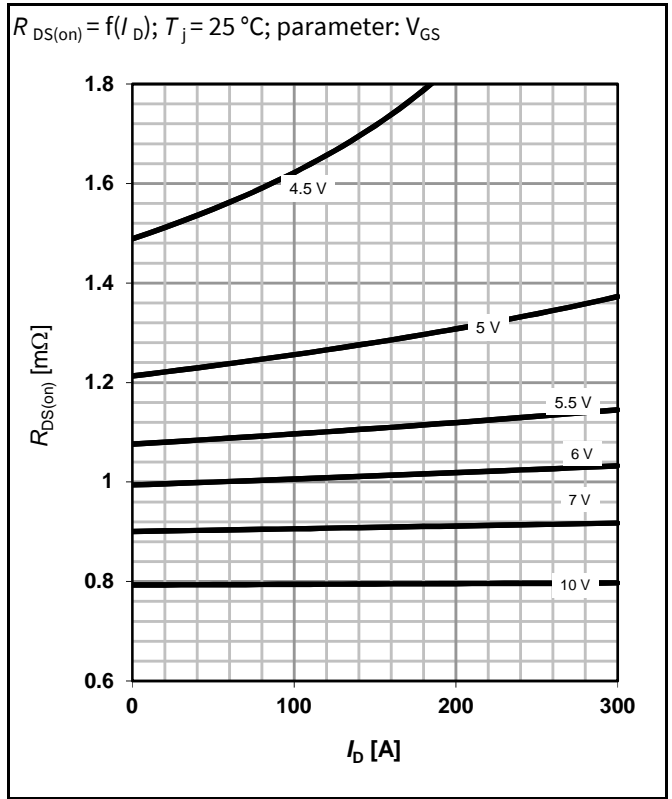
### 4 Max. transient thermal impedance



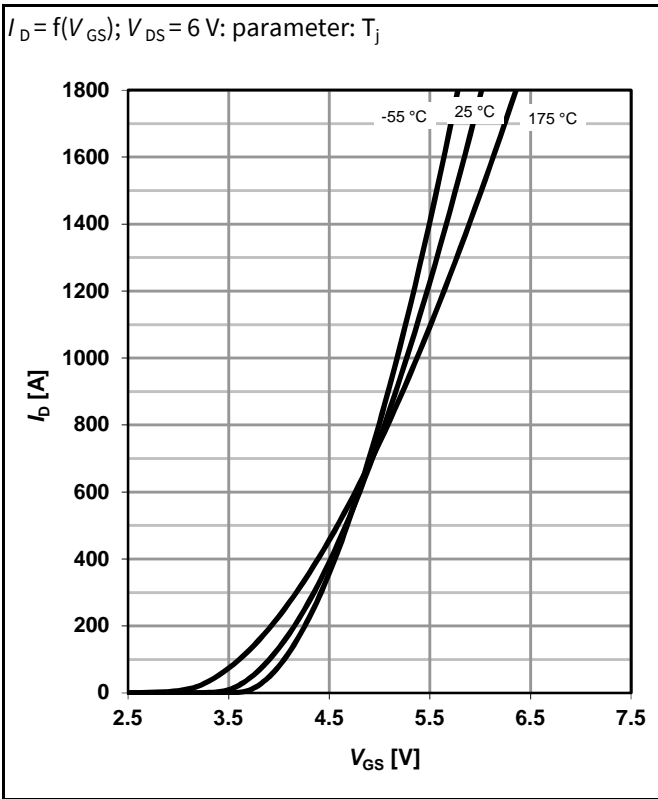
5 Typ. output characteristics



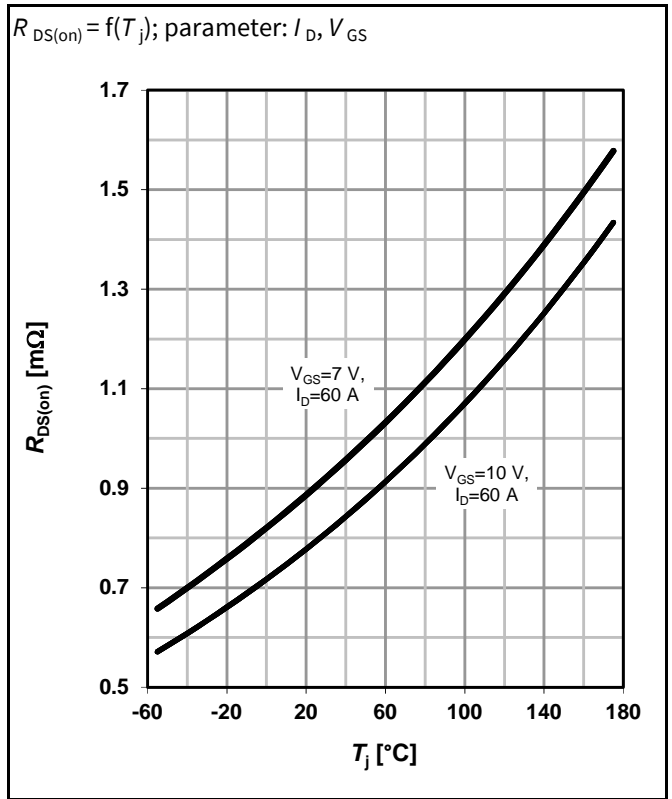
6 Typ. drain-source on-state resistance



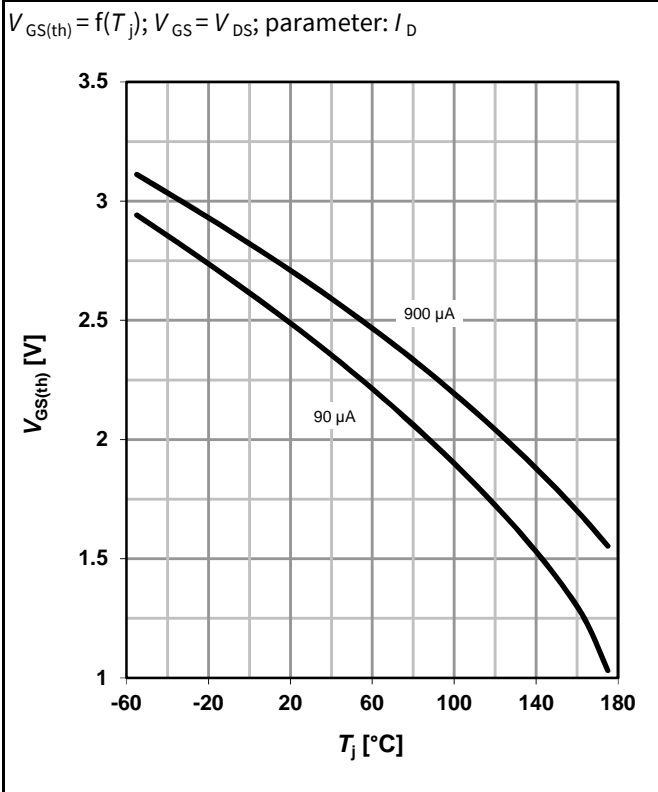
7 Typ. transfer characteristics



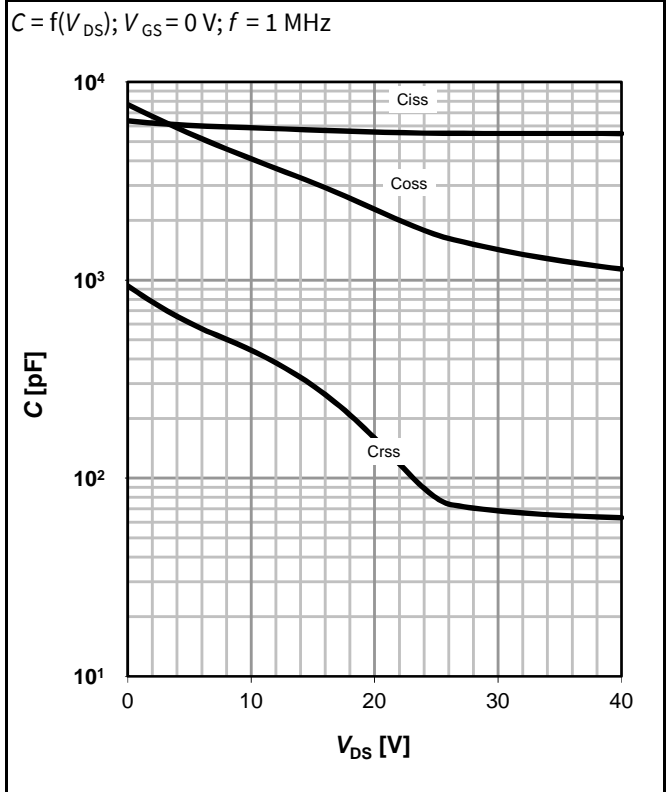
8 Typ. drain-source on-state resistance



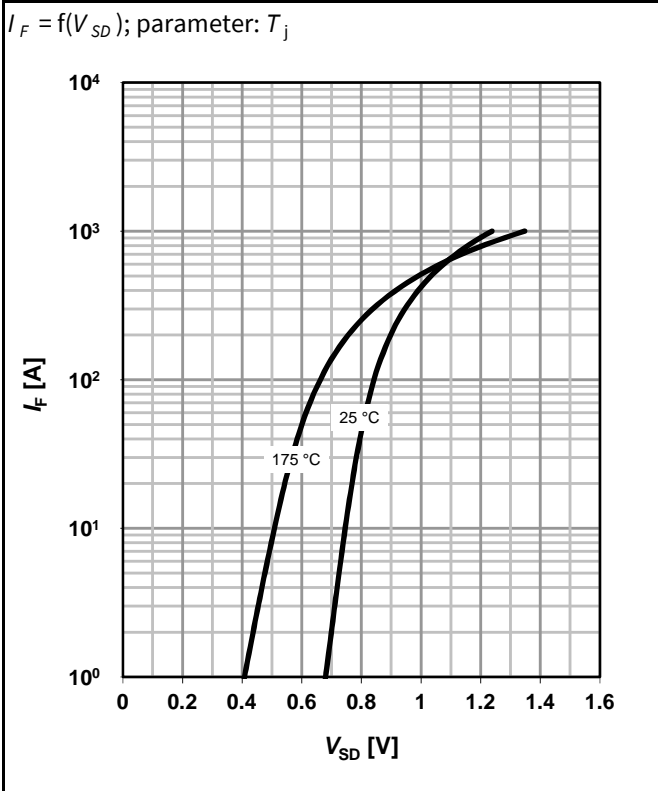
9 Typ. gate threshold voltage



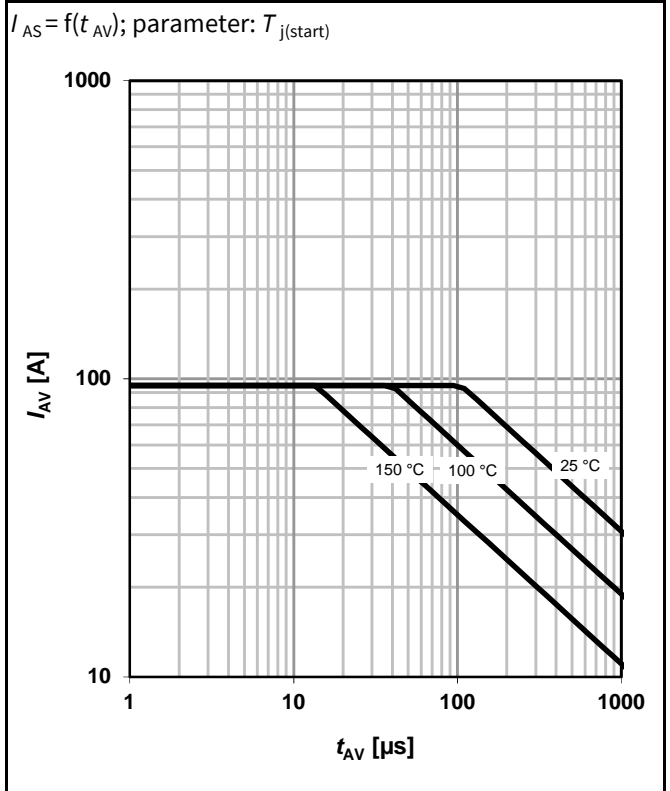
10 Typ. capacitances



11 Typical forward diode characteristics

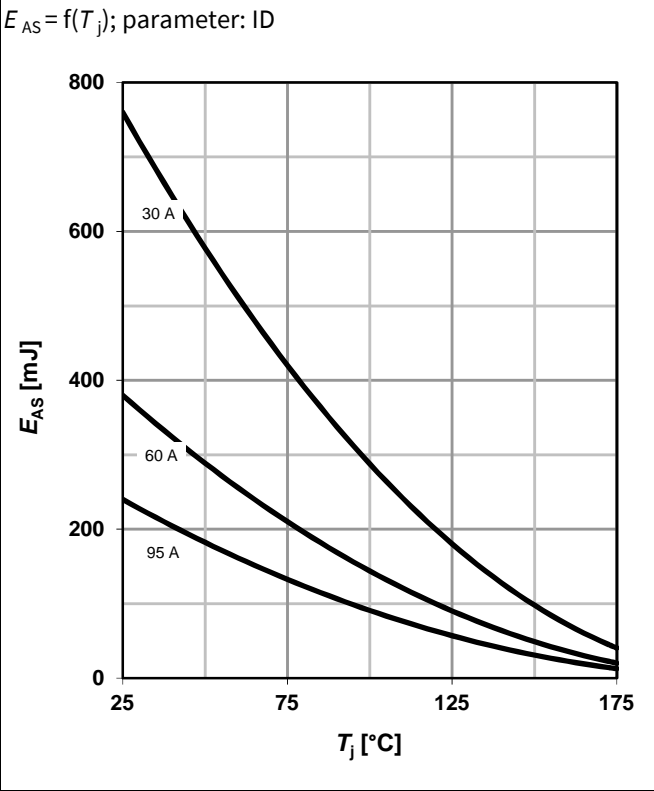


12 Typ. avalanche characteristics

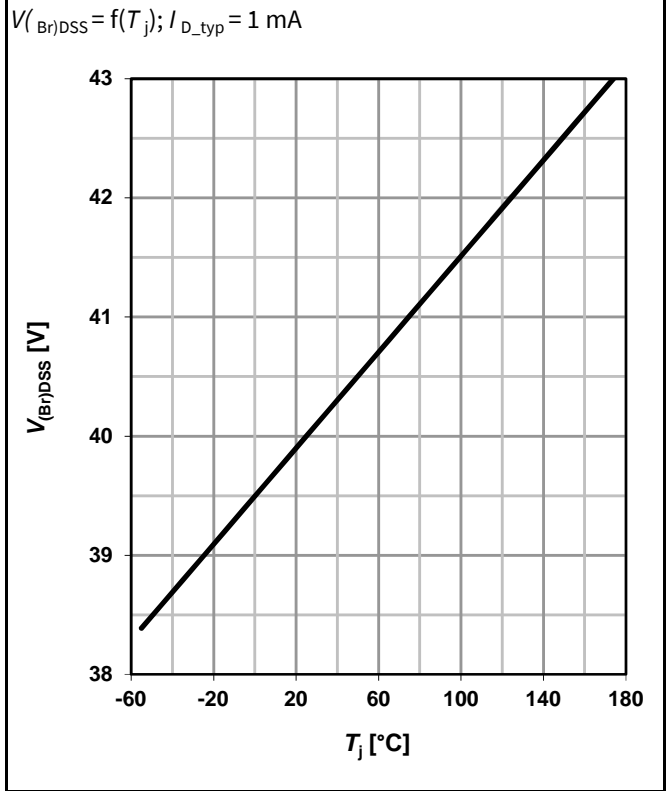




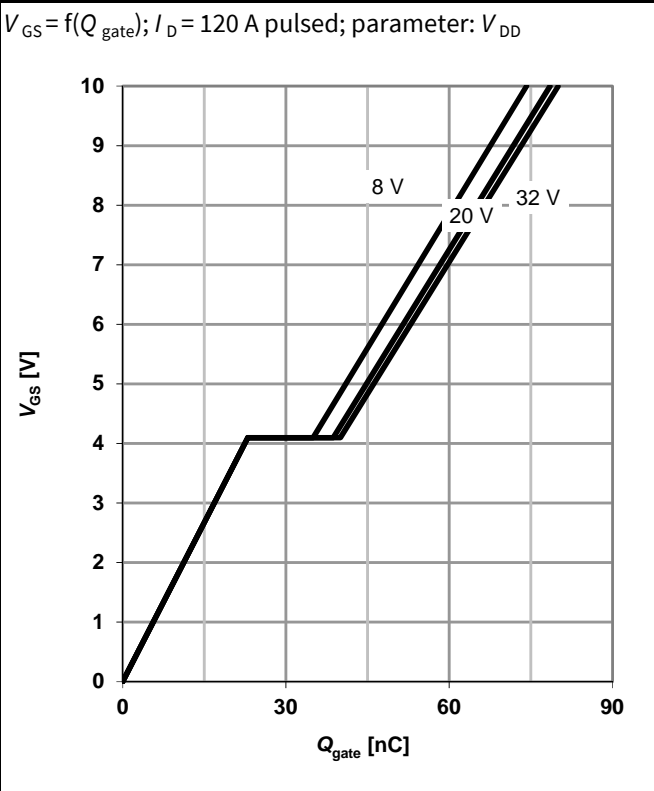
13 Typical avalanche energy



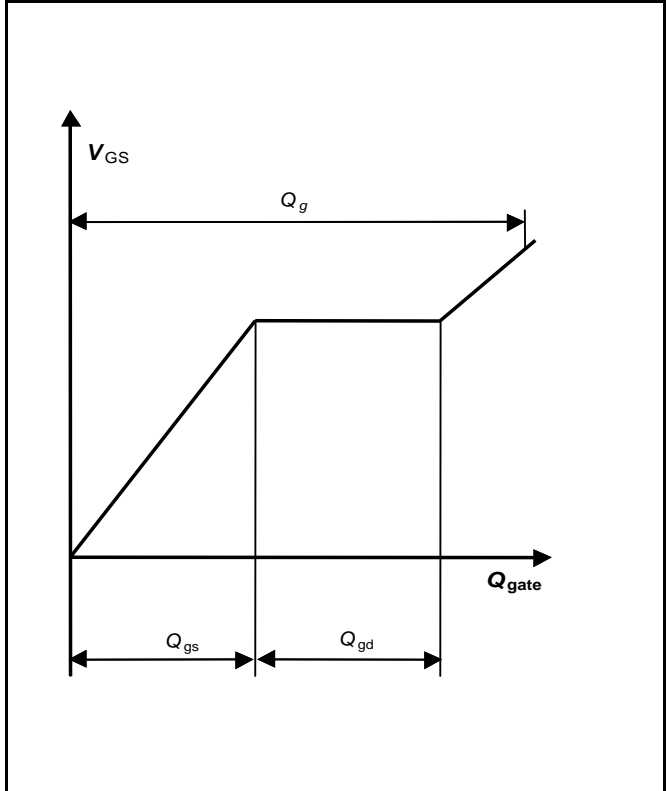
14 Drain-source breakdown voltage



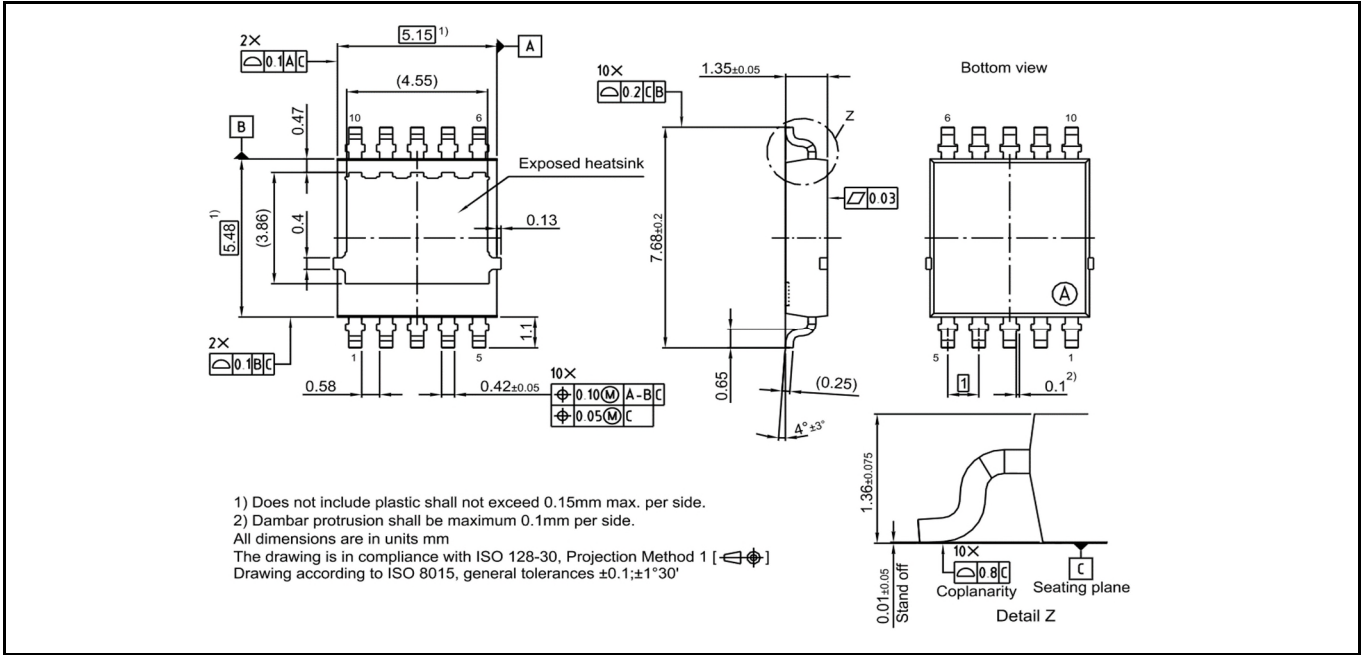
15 Typ. gate charge



16 Gate charge waveforms

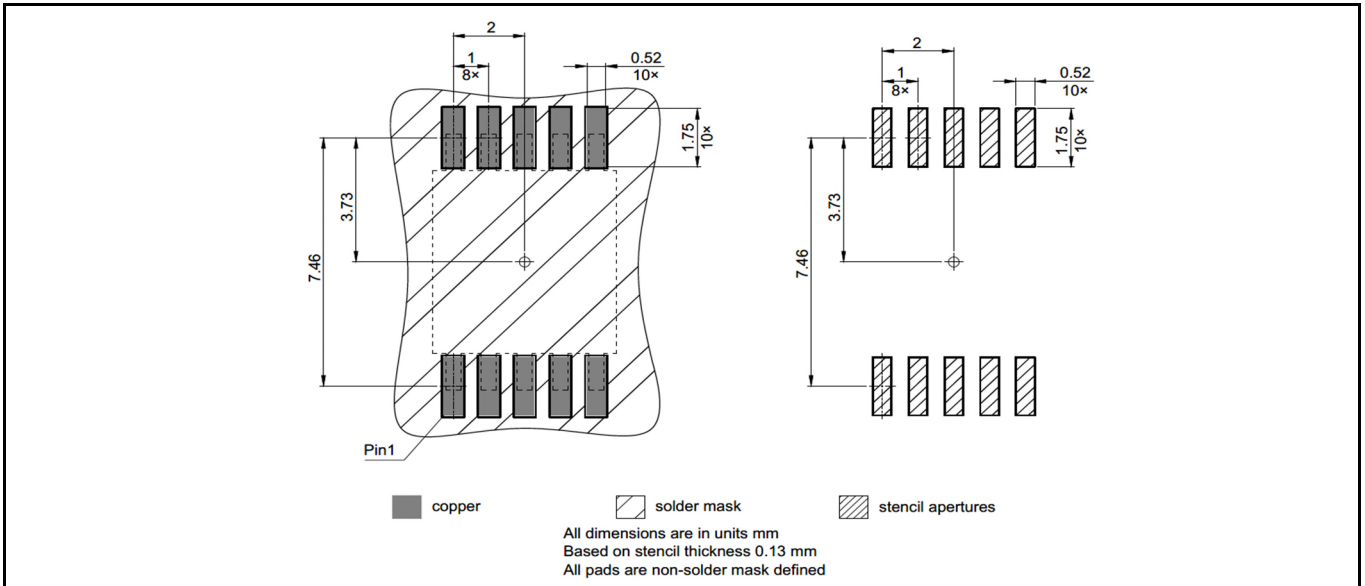


## Package Outline

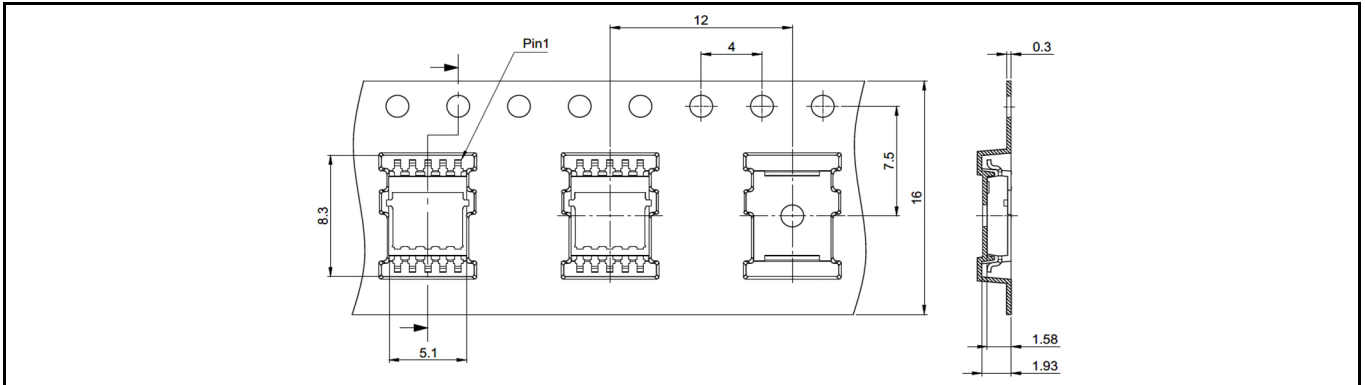


<https://www.infineon.com/cms/en/product/packages/PG-LHDSO/PG-LHDSO-10-2>

## Footprint



## Packaging



all dimensions in mm



## Revision History

Revision	Date	Changes
Revision 1.1	21.08.2023	Final Data Sheet

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[1EDC20H12AH](#) [1EDC20H12AHXUMA1](#)